

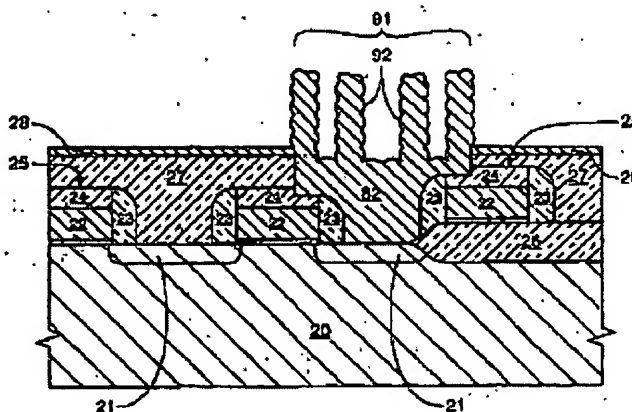
**Conducting structure prodn. on topography of substrate**

**Patent number:** DE4447804  
**Publication date:** 2002-01-24  
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**Classification:**  
- international: H01L21/8242  
- european: H01L21/02B3; H01L21/02B3C; H01L21/02B3C2; H01L21/768; H01L21/8242B2; H01L27/108F2  
**Application number:** DE19944447804 19940209  
**Priority number(s):** DE19944404129 19940209; US19930017067 19930212

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**Abstract of DE4447804**

Prodn. of a conducting structure having several pins on the topography of a starting substrate comprises: (a) forming 1st, 2nd and 3rd insulating layers (27,28,29) completely over the topography; (b) patterning and etching an opening (30) in the 3 insulating layers; (c) forming and planarising a conducting layer (31) by filling the opening; (d) creating an etching mask (33) by applying polysilicon having semispherical grain size for pattern transfer; (e) transferring an archipelago pattern over the etching mask onto the planar conducting layer; and (f) forming pins (34) to create the conducting structure having the several pins.



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